Silicon Power Transistors

	Type No.	Case	Construction (see note 1)	Maximum Ratings at T_{case} = 25°C					Typical Performance								NOTES
				V_{CBO} V	V_{CEO} V	V_{EBO} V	$I_{C(DC)}$ A	P_{tot} W	f MHz	V_{CC} V	P_{IN} W	P_{OUT} W	n_C[2] %	f_T MHz	C_{OB} pF	sc/oc[3]	
VHF NPN Power Devices	2N3866	TO39	EP	55	30	4	0·5	5·0	400	28	0·1	1·2	45	800	2·5	—	
	XB401	TO39	EP	65	40	4	1·0	7·0	175	28	0·4	2·8	70	500	6·0	—	
	2N3375	TO60	EP	65	40	4	1·5	11·6	175	28	1·0	8·0	70	500	9·0	√	
	XB404	TO60	EP	65	40	4	3·0	23	175	28	2·0	12·0	75	500	13·0	√	
	2N3632	TO60	EP	65	40	4	3·0	23	175	28	3·5	15·0	80	400	18·0	√	
	XB408	TO60	EP	65	40	4	5·0	30	175	28	9·0	27·0	80	400	18·0	√	
	XB409	TO60	EP	65	40	4	7·5	30	175	28	6·0	27·0	75	400	18·0	√	Typical 10 W AM
	2N4128	TO117	EP	65	40	4	5·0	35	175	25	6·0	27·0	75	400	18·0	√	
VHF NPN FM Amplifier	XB411	TO39	EP	40	25	4	1·0	5	175	13·5	0·25	1·2	45	500	16·0	—	13 W FM Kit
	XB412	TO117	EP	40	25	4	1·5	10	175	13·5	1·0	5·0	70	400	16·0	—	
	XB413	TO177	EP	40	25	4	3·0	25	175	13·5	4·0	13·0	80	400	32·0	√	
VHF NPN AM Amplifier	XB421	TO39	EP	65	40	4	1·0	5	175	12·5	0·3	1·0	60	400	16	—	10 W AM Kit
	XB422	TO117	EP	65	40	4	1·5	10	175	12·5	1	3	65	400	24	—	
	XB423	TO117	EP	65	40	4	5·0	30	175	12·5	3	10	70	400	32	√	

	Type No.	Case	Construction (see note 1)	Maximum Ratings at T_{case} = 25°C					Characteristics T_{case} = 25°C								NOTES
									h_{FE}			$V_{CE(SAT)}$			Min.	Max.	
				V_{CBO} V	V_{CEO} V	V_{EBO} V	$I_{C(DC)}$ A	P_{tot}[4] W	I_C A	Min.	Max.	I_C A	I_C A	Max. V	f_T MHz	T_{OFF} µs	
NPN Medium Power	2N1714	TO5	3DM		60	6	0·75	10^2	0·2	20	60	0·2	0·02	2·0	16		Under max. ratings column P_{tot} should read see note 4
	2N1715	TO5			100	6	0·75	10^2	0·2	20	60	0·2	0·02	2·0	16		
	2N1716	TO5			60	6	0·75	10^2	0·2	40	120	0·2	0·02	2·0	16		
	2N1717	TO5			100	6	0·75	10^2	0·2	40	120	0·2	0·02	2·0	16		
	2N1718	T.SLUG			60	6	0·75	10^2	0·2	20	60	0·2	0·02	2·0	16		
	2N1719	T.SLUG			100	6	0·75	10^2	0·2	20	60	0·2	0·02	2·0	16		
	2N1720	T.SLUG			60	6	0·75	10^2	0·2	40	120	0·2	0·02	2·0	16		
	2N1721	T.SLUG			100	6	0·75	10^2	0·2	40	120	0·2	0·02	2·0	16		
	2N4000	TO5		100	80	8	1	15^2	0·5	30	120	1·0	0·1	0·5	40	2	
	2N4001	TO5		120	100	8	1	15^2	0·5	40	120	1·0	0·1	0·5	40	2	
	2N4300	TO5		100	80	8	2	15^2	1·0	30	120	2·0	0·2	0·5	30	1·5	
	2N3418	TO5	EP	85	60	8	3	10^2	1·0	20	60	2·0	0·2	0·5	40	1·2	
	2N3419	TO5		125	80	8	3	10^2	1·0	20	60	2·0	0·2	0·5	40	1·2	
	2N3420	TO5		85	60	8	3	10^2	1·0	40	120	2·0	0·2	0·5	40	1·2	
	2N3421	TO5		125	80	8	3	10^2	1·0	40	120	2·0	0·2	0·5	40	1·2	

NOTE 1: The following symbols have been used throughout the Product Summary:

Under "Construction":
A — Alloyed
D — Diffused
E — Epitaxial
G — Grown
M — Mesa
P — Planar

Under h_{FE}:
* — h_{fe}

Under f_T:
φ — f_{hfb}
△ — f_{hfe}
‡ — typical

Under Dissipation:
† — dissipation at T_{case} = 25°C

NOTE 2: Collector efficiency=($P_{OUT} \div P_{DC}$) x 100%. No account is taken of P_{IN}.
NOTE 3: Passes Texas Instruments load open/short circuit test.
NOTE 4: T_{case}=100°C.